

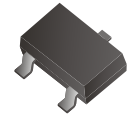
# SMD Switching Diode



SMD Diodes Specialist

## CDST116-G

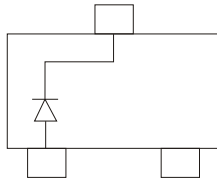
RoHS Device



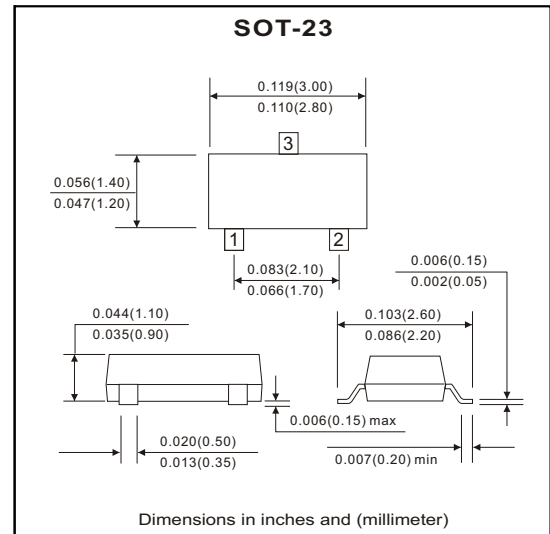
### Features

- Low leakage current applications.
- Medium speed switching times.

### Polarity:



### Marking: JV



### Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	75	V
Forward continuous current	$I_{FM}$	215	mA
Power dissipation	$P_D$	250	mW
Junction temperature	$T_J$	150	°C
Storage temperature	$T_{STG}$	-55 to +150	°C

### Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ.	Max	Unit
Reverse breakdown voltage	$I_R=100\mu A$	$V_{(BR)R}$	75			V
Forward voltage	$I_F=1mA$	$V_{F1}$			0.9	V
	$I_F=10mA$	$V_{F2}$			1	V
	$I_F=50mA$	$V_{F3}$			1.1	V
	$I_F=150mA$	$V_{F4}$			1.25	V
Reverse current	$V_R=75V$	$I_R$			5	$\mu A$
Capacitance between terminals	$V_R=0V, f=1MHz$	$C_T$		2		pF
Reverse recovery time	$I_F=I_R=10mA, I_{rr}=0.1 \times I_R, R_L=100\Omega$	$t_{rr}$			3	nS

## RATING AND CHARACTERISTIC CURVES (CDST116-G)

Fig.1 Forward Current Derating Curve

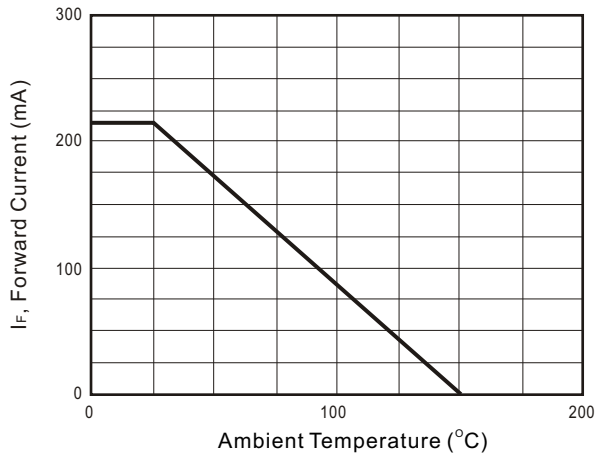


Fig.2 Forward Voltage Characteristics

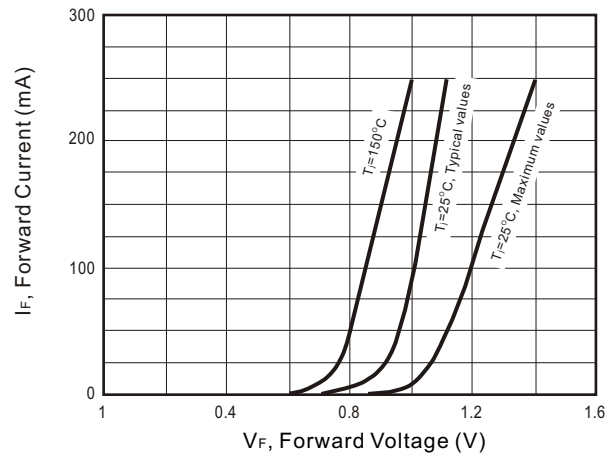


Fig.3 Reverse Characteristics

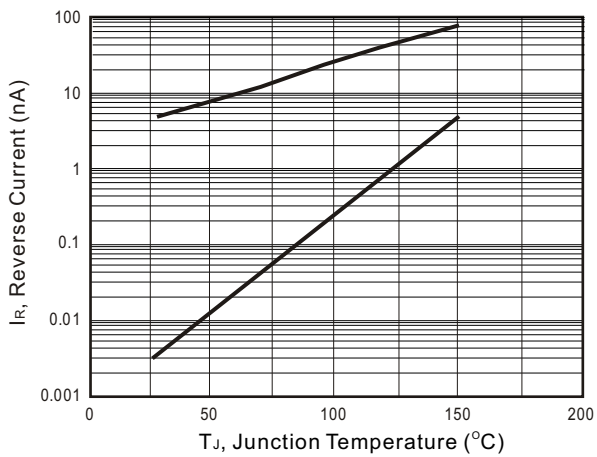


Fig.4 Diode Capacitance Characteristics

